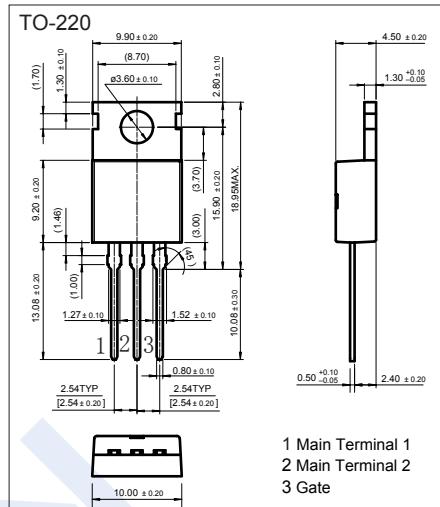
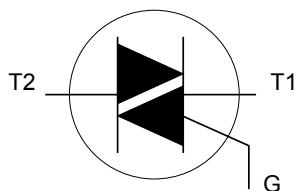


## TRIACS Thyristor

### BT137-600E

#### ■ Features

- Repetitive peak off-state voltages :600V
- RMS on-state current :8A
- Non-repetitive peak on-state current :65A



#### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Peak Repetitive Forward and Reverse Blocking Voltages	V <sub>DRM</sub> V <sub>RRM</sub>	600	V
RMS on-state Current @ full sine wave; T <sub>mb</sub> ≤ 102 °C	I <sub>T</sub> (RMS)	8	
Non-Repetitive Peak on-state Current (t=20ms)	I <sub>TS</sub> M	65	A
Non-Repetitive Peak on-state Current (t=16.7ms)		71	
Circuit Fusing Considerations (t = 10ms)	I <sup>2</sup> t	21	A <sup>2</sup> s
Peak Gate Current	I <sub>GM</sub>	2	A
Peak Gate Voltage	V <sub>GM</sub>	5	V
Peak Gate Power	P <sub>GM</sub>	5	
Average Gate Power	P <sub>G(AV)</sub>	0.5	
Thermal Resistance Junction to Ambient	R <sub>thJA</sub>	60	
Thermal Resistance Junction to Mounting Base @ full cycle	R <sub>thJB</sub>	2	K/W
Thermal Resistance Junction to Mounting Base @ half cycle		2.4	
junction Temperature	T <sub>J</sub>	125	
Storage Temperature range	T <sub>stg</sub>	-40 to 150	°C

## TRIACS Thyristor

### BT137-600E

■ Electrical Characteristics ( $T_a = 25^\circ\text{C}$ , unless otherwise noted.)

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Unit
Repetitive Peak off-state Voltages	$V_{DRM}$	$I_D=I_R=50\mu\text{A}$	600			V
Off-state Leakage Current	$I_D$	$V_{DRM(\text{Max})}=V_D, T_J=125^\circ\text{C}$			0.5	mA
On-state Voltage	$V_{TM}$	$I_T=10\text{A}$			1.65	
Gate Trigger Voltage	$V_{GT}$	$V_D=12\text{V}, I_T=100\text{mA}$			1.5	V
		$V_D=400\text{V}, I_T=100\text{mA}, T_J=125^\circ\text{C}$	0.25			
Gate Trigger Current	$I_{GT}$	$V_D=12\text{V}, I_T=100\text{mA}$	$T_2+ G+$		25	mA
			$T_2+ G-$		25	
			$T_2- G-$		25	
			$T_2- G+$		70	
Latching Current	$I_L$	$V_D=12\text{V}, I_{GT}=100\text{mA}$	$T_2+ G+$		30	mA
			$T_2+ G-$		45	
			$T_2- G-$		30	
			$T_2- G+$		45	
Holding Current	$I_H$	$V_D=12\text{V}; I_G=100\text{mA}$			20	
Repetitive Rate of rise of on-state Current after Triggering	$dI/dt$		$T_2+ G+$		50	A/us
			$T_2+ G-$		50	
			$T_2- G-$		50	
			$T_2- G+$		10	
Critical Rate of rise of off-state Voltage	$dV_D/dt$	$V_{DM}=67\% V_{DRM(\text{max})}; T_J=125^\circ\text{C}$ exponential waveform; gate open circuit	50	250		V/us
Critical Rate of Change of Commutating Voltage	$dV_{com}/dt$	$V_{DM}=400\text{V}; T_J=95^\circ\text{C}; I_T(\text{RMS}) = 8 \text{ A};$ $dI_{com}/dt = 3.6 \text{ A/ms}$ ; gate open circuit		20		
Gate Controlled turn-on time	$t_{gt}$	$I_{TM}=12\text{A}; V_D=V_{DRM(\text{max})}, I_G=100\text{mA};$ $dI_G/dt=5\text{A/us}$		2		us

## TRIACS Thyristor

### BT137-600E

#### ■ Typical Characteristics

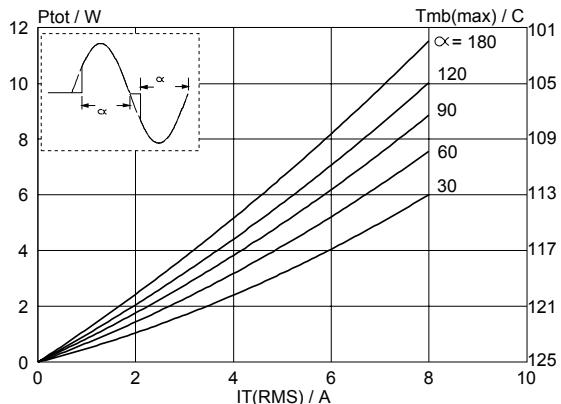


Fig. 1. Maximum on-state dissipation,  $P_{tot}$ , versus rms on-state current,  $I_{T(RMS)}$ , where  $\alpha$  = conduction angle.

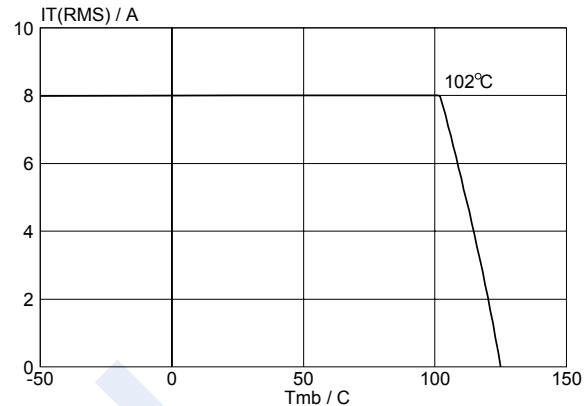


Fig.4. Maximum permissible rms current  $I_{T(RMS)}$ , versus mounting base temperature  $T_{mb}$ .

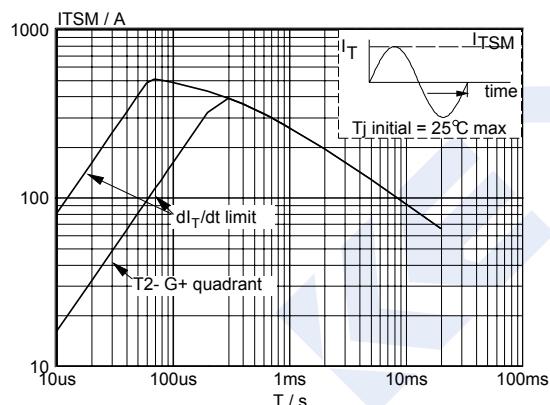


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \leq 20ms$ .

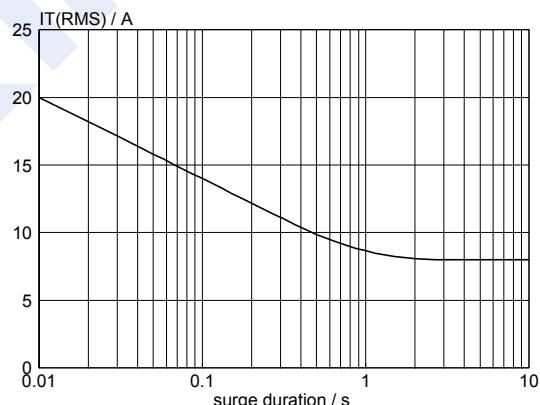


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents,  $f = 50$  Hz;  $T_{mb} \leq 102^\circ C$ .

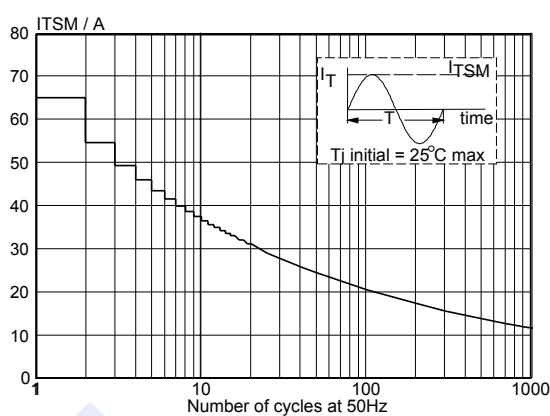


Fig.3. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents,  $f = 50$  Hz.

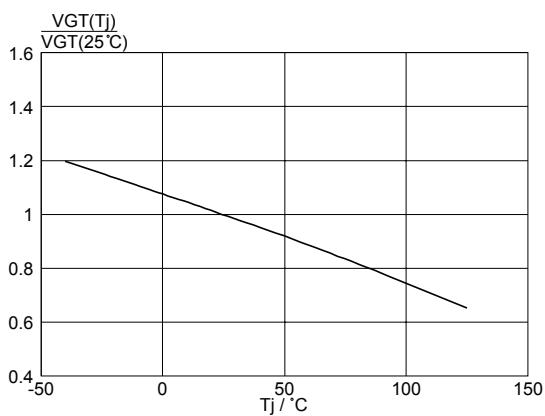


Fig.6. Normalised gate trigger voltage  $V_{GT}(T_j)/V_{GT}(25^\circ C)$ , versus junction temperature  $T_j$ .

## TRIACS Thyristor

## BT137-600E

## ■ Typical Characteristics

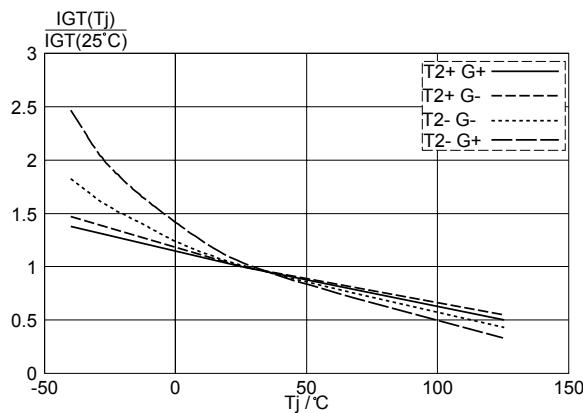


Fig.7. Normalised gate trigger current  $I_{GT}(T_j)/I_{GT}(25^\circ\text{C})$ , versus junction temperature  $T_j$ .

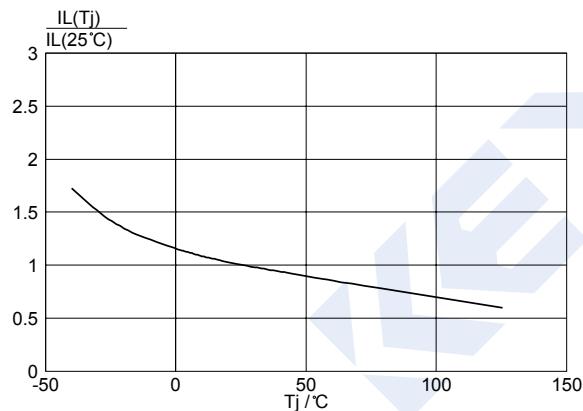


Fig.8. Normalised latching current  $I_L(T_j)/I_L(25^\circ\text{C})$ , versus junction temperature  $T_j$ .

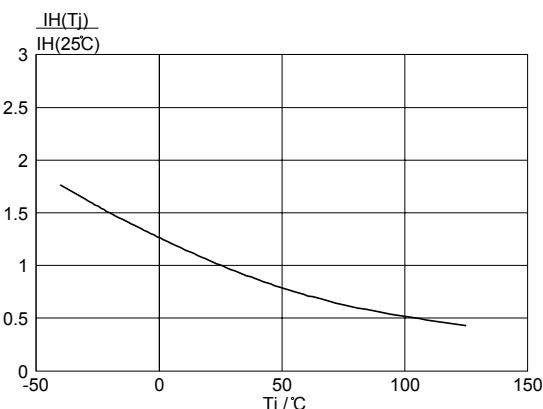


Fig.9. Normalised holding current  $I_H(T_j)/I_H(25^\circ\text{C})$ , versus junction temperature  $T_j$ .

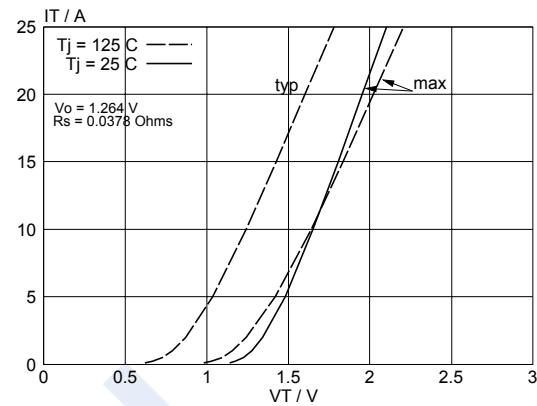


Fig.10. Typical and maximum on-state characteristic.

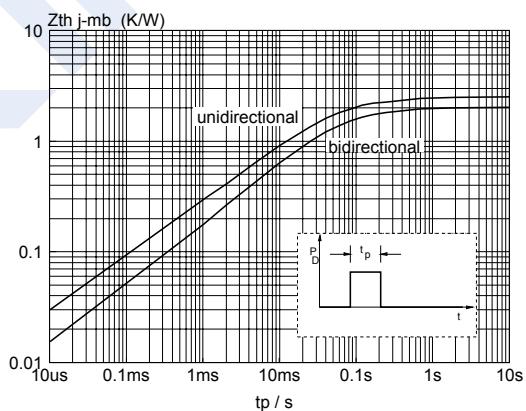


Fig.11. Transient thermal impedance  $Z_{th\ j\ -mb}$  pulse width  $t_p$ .

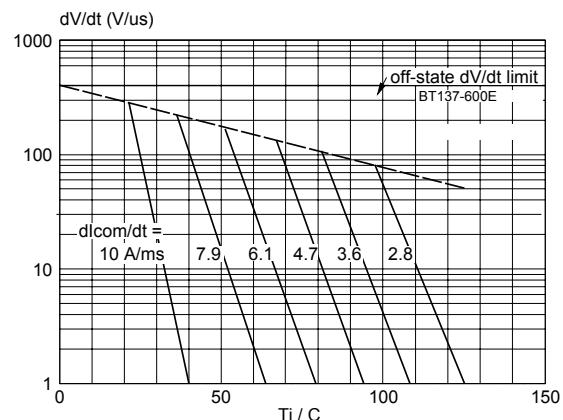


Fig.12. Typical commutation  $dV/dt$  versus junction temperature, parameter commutation  $dl_T/dt$ . The triac should commutate when the  $dV/dt$  is below the value on the appropriate curve for pre-commutation  $dl_T/dt$ .